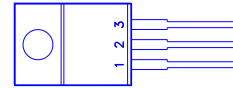
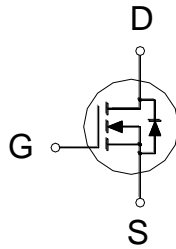




**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D^2$
100V	6.5mΩ	120A



- 1. GATE
- 2. DRAIN
- 3. SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ °C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current <sup>2</sup>	$T_C = 25\text{ °C}$	$I_D$	120	A
	$T_C = 100\text{ °C}$		76	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	375	
Avalanche Current		$I_{AS}$	39	
Avalanche Energy	$L = 1\text{mH}$	$E_{AS}$	770	mJ
Power Dissipation	$T_C = 25\text{ °C}$	$P_D$	208	W
	$T_C = 100\text{ °C}$		83	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		0.6	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Package limitation current is 110A

**ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ °C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.8	2.3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125\text{ °C}$			10	

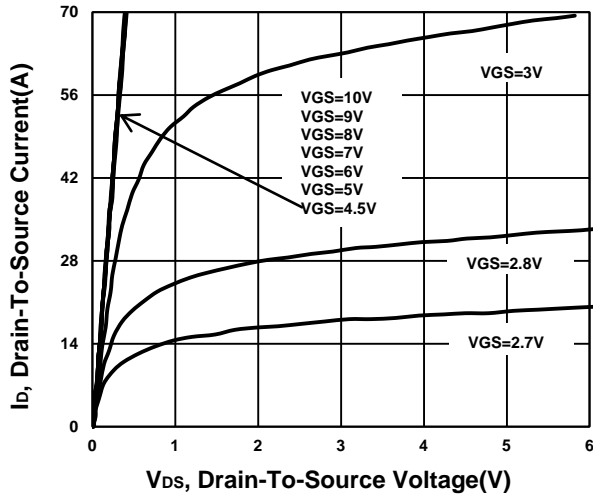
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 20A$	5.8	8	mΩ		
		$V_{GS} = 10V, I_D = 20A$	5.3	6.5			
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 10V, I_D = 20A$	140		S		
<b>DYNAMIC</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	6188		pF		
Output Capacitance	$C_{oss}$		747				
Reverse Transfer Capacitance	$C_{rss}$		233				
Gate Resistance	$R_g$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$	1.26		Ω		
Total Gate Charge <sup>2</sup>	$Q_{g(VGS=10V)}$	$V_{DS} = 50V, I_D = 20A$	121		nC		
	$Q_{g(VGS=4.5V)}$		64.2				
Gate-Source Charge <sup>2</sup>	$Q_{gs}$		15.8				
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$		30				
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$		$V_{DD} = 50V,$ $I_D \cong 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$	20			nS
Rise Time <sup>2</sup>	$t_r$			60			
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$	55					
Fall Time <sup>2</sup>	$t_f$	57					
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)</b>							
Continuous Current <sup>3</sup>	$I_S$			120	A		
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = 20A, V_{GS} = 0V$		1.2	V		
Reverse Recovery Time	$t_{rr}$	$I_F = 20A, di/dt = 100A/\mu s$	58		nS		
Reverse Recovery Charge	$Q_{rr}$		136		nC		

<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

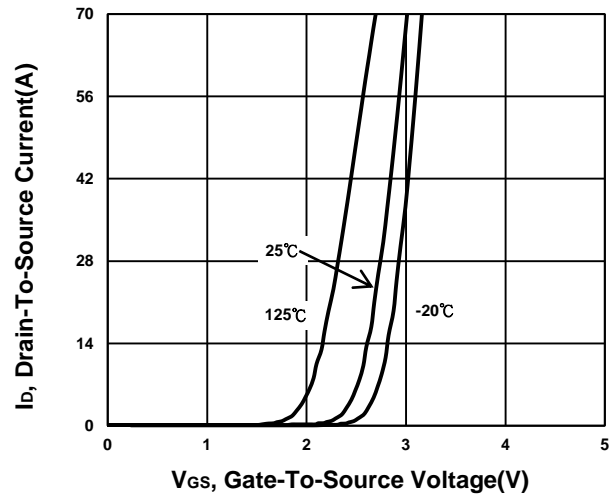
<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Package limitation current is 110A

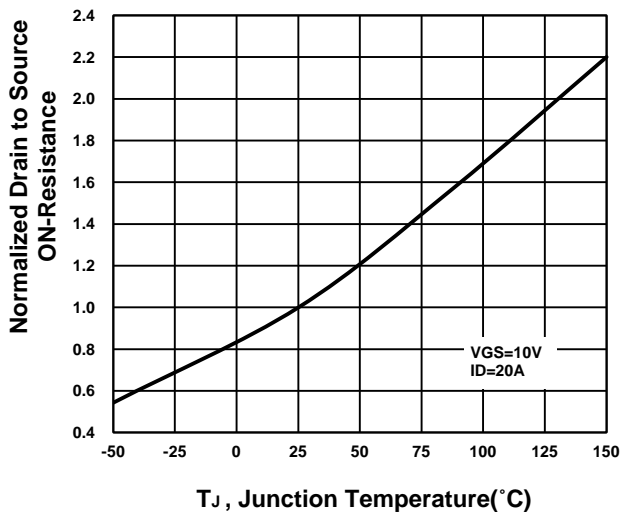
**Output Characteristics**



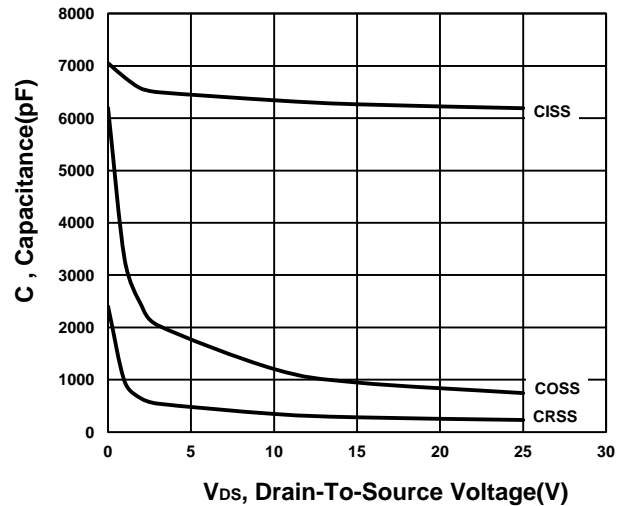
**Transfer Characteristics**



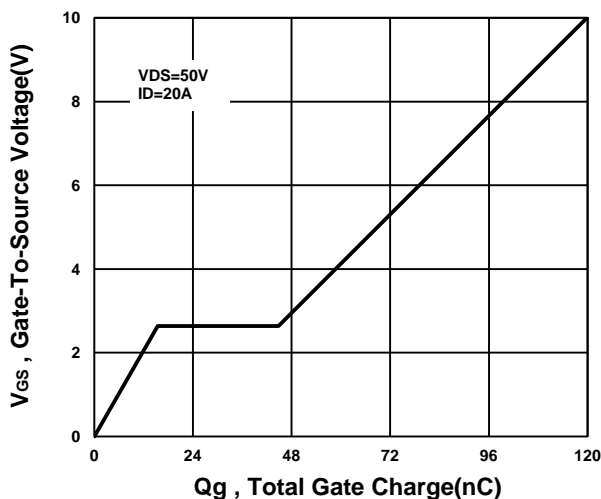
**On-Resistance VS Temperature**



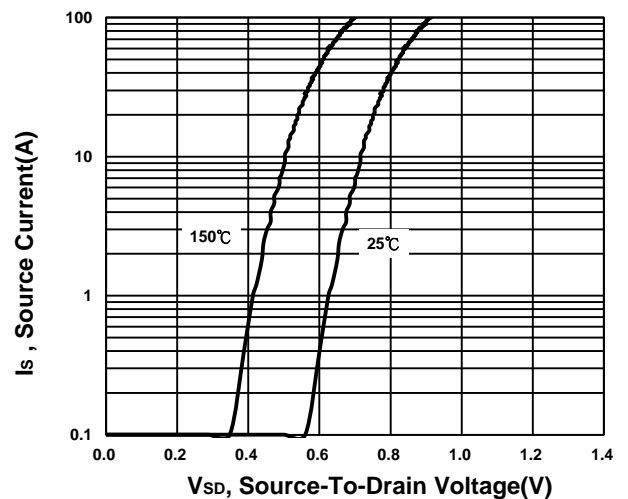
**Capacitance Characteristic**



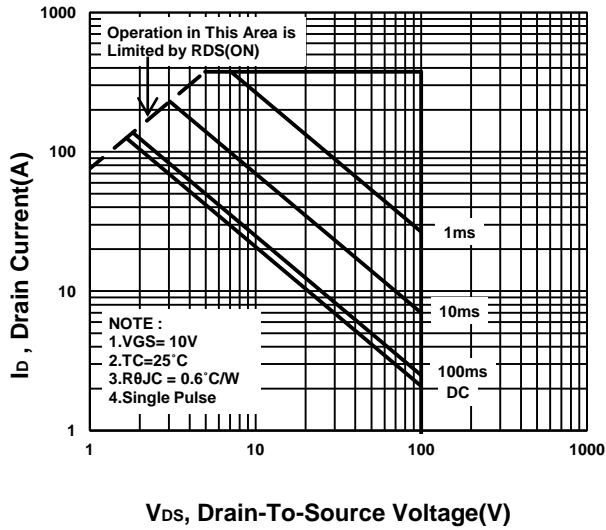
**Gate charge Characteristics**



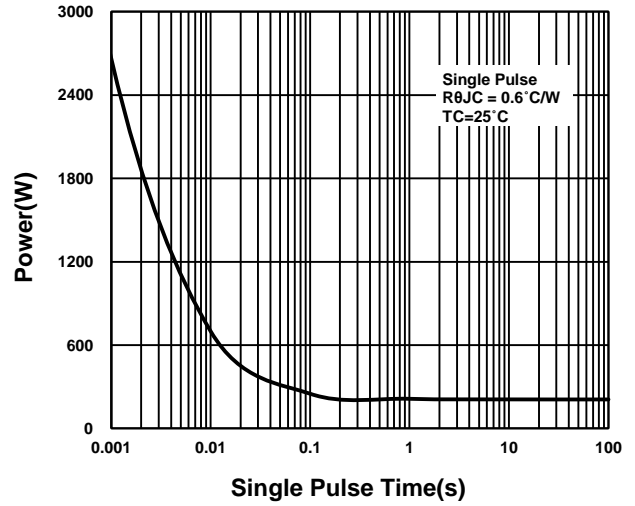
**Source-Drain Diode Forward Voltage**



**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**

